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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/904,360	07/12/2001	Giuseppe Curello	Z&PINFP-08190	1413
24131	7590 09/21/2004		EXAMINER	
LERNER A	ND GREENBERG, PA	ANYA, IGWE U		
P O BOX 248	30 DD, FL 33022-2480		ART UNIT	PAPER NUMBER
HOLLI WOO	D, 12 33022-2-100		2825	
			DATE MAILED: 09/21/2004	4

Please find below and/or attached an Office communication concerning this application or proceeding.

<u>:                                      </u>		Application No.	Applicant(s)	
Office Action Summary		09/904,360 CURELLO ET		
		Examiner	Art Unit	
		Igwe U. Anya	2825	a~/
Period fo	The MAILING DATE of this communication	n appears on the cover shee	t with the correspondence addi	ress
A SH THE   - Exter after - If the - If NO - Failu Any	ORTENED STATUTORY PERIOD FOR R MAILING DATE OF THIS COMMUNICATI nsions of time may be available under the provisions of 37 C SIX (6) MONTHS from the mailing date of this communicati period for reply specified above is less than thirty (30) days period for reply is specified above, the maximum statutory re to reply within the set or extended period for reply will, by reply received by the Office later than three months after the red patent term adjustment. See 37 CFR 1.704(b).	ON.  FR 1.136(a). In no event, however, ma on. , a reply within the statutory minimum o period will apply and will expire SIX (6) I statute, cause the application to becom	ny a reply be timely filed f thirty (30) days will be considered timely. MONTHS from the mailing date of this com the ABANDONED (35 U.S.C. § 133).	nmunication.
Status				
1)⊠ 2a)□ 3)□	Responsive to communication(s) filed on This action is <b>FINAL</b> . 2b) Since this application is in condition for all closed in accordance with the practice un	This action is non-final. lowance except for formal n		merits is
Dispositi	on of Claims			
5)⊠ 6)⊠ 7)⊠	Claim(s) <u>1-21</u> is/are pending in the applic 4a) Of the above claim(s) is/are wit Claim(s) <u>21</u> is/are allowed. Claim(s) <u>1-4 and 8-12</u> is/are rejected. Claim(s) <u>5-7 and 13-20</u> is/are objected to Claim(s) are subject to restriction a	hdrawn from consideration.		
Applicati	ion Papers			
10)⊠	The specification is objected to by the Example The drawing(s) filed on 12 July 2001 is/are Applicant may not request that any objection to Replacement drawing sheet(s) including the country The oath or declaration is objected to by the	e: a) $\boxtimes$ accepted or b) $\square$ obsorbed in absorbed in absorbed in absorbed if the drawn are the draw	eyance. See 37 CFR 1.85(a). ving(s) is objected to. See 37 CFR	` '
Priority (	ınder 35 U.S.C. § 119			
a)l	Acknowledgment is made of a claim for fo  All b) Some * c) None of:  1. Certified copies of the priority docu 2. Certified copies of the priority docu 3. Copies of the certified copies of the application from the International Beet the attached detailed Office action for	ments have been received. ments have been received i e priority documents have be sureau (PCT Rule 17.2(a)).	n Application No een received in this National S	tage
Attachmen	t(s)			
2) 🔲 Notic 3) 🔲 Infori	e of References Cited (PTO-892) e of Draftsperson's Patent Drawing Review (PTO-94 mation Disclosure Statement(s) (PTO-1449 or PTO/S r No(s)/Mail Date	8) Paper	ew Summary (PTO-413) No(s)/Mail Date of Informal Patent Application (PTO-1	152)

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### **DETAILED ACTION**

### Claim Rejections - 35 USC § 102

1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- 2. Claims 1 3, 8, 9, 10, 11, are rejected under 35 U.S.C. 102(b) as being anticipated by Kameyama et al. (US Patent 5296388).
- 3. Kameyama et al. (fig. 2) teach producing a doping (112) at a surface silicon substrate (106P) by arsenic ion implantation, wherein the doping destroys a natural oxide on the semiconductor substrate and transforms the doped region (112) into an amorphous structure (col. 8 lines 5 13), after the doping, depositing a polysilicon layer (114) at the surface (fig. 3), and then annealing to produce an epitaxial layer and a buried doping (col. 8 lines 14 35). Kameyama et al. further teach the doping can be achieved by ion implantation with ions selected from Si, Ge, and Ar (col. 17 lines 26 37). The semiconductor substrate comprising of silicon (col. 8 lines 64 –68).

## Claim Rejections - 35 USC § 103

- 4. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
  - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the

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invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

- 5. Claims 4 and 12 are rejected under 35 U.S.C. 103(a) as being unpatentable over Kameyama et al. (US Patent 5296388).
- 6. The Kameyama et al. reference teaches the feature previously outlined, but lacks the amorphous layer to have a thickness of 500 1000 nm, and depositing the polysilicon layer by LPCVD.
- 7. However, it would have been obvious to one of ordinary skill in the art at the time the invention was made to deposit the amorphous layer to a thickness of 500 1000 nm, and depositing the polysilicon layer by LPCVD, since it has been held that provision for adjustability where needed, involves only routine skill in the art. In re Stevens, 101 USPQ 284 (CCPA 1954).
- 8. Claims 5-7, and 13-20 are objected to as being dependent upon a rejected claim, but would be allowable if rewritten in independent form.
- 9. Claim 21 is allowable, because prior does not teach inter alia a polycrystalline or amorphous layer on a doped surface subjected to ion bombardment or RTA ,and further subjected to heat treatment to produce a MOS transistor.

#### Remarks

10. Applicant's arguments filed June 29, 2004 have been fully considered but they are not persuasive. Kameyama et al. is not doping through the oxide, rather oxide (108) is used as a mask for doping through the aperture (see fig. 2, & col. 7 lines 64 – 67). The Declaration filed on June 29, 2004 under 37 CFR 1.131 is sufficient to overcome the Yu reference.

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### **Contact Information**

11. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Igwe U. Anya whose telephone number is (571) 272-1887. The examiner can normally be reached on M - F 8:30am - 5:00pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Matthew S. Smith can be reached on (751) 272-1907. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Igwe U. Anya Examiner Art Unit 2825

IA

March 19, 2004

MATTHEW SMITH
SUPERVISORY PATENT EXAMINER
TECHNOLOGY CESTER COSC